

IN THE CLAIMS

Claims 1-6 (Canceled).

7 (Currently Amended). A method comprising:

forming a dielectric using a metallic precursor directly on a semiconductor substrate; and
oxidizing said metallic precursor in a liquid.

8 (Original). The method of claim 7 including using a liquid oxidizer.

9 (Original). The method of claim 7 using an oxidizer in an aqueous solution.

10 (Original). The method of claim 7 including forming a metal oxide dielectric over a silicon substrate.

11 (Original). The method of claim 10 including forming a metal oxide dielectric of hafnium, zirconium, or tantalum.

12 (Original). The method of claim 7 including depositing a metallic film using physical vapor deposition.

13 (Original). The method of claim 7 including oxidizing using a liquid oxidizer selected from the group including solutions of O₃, H₂O₂, and organic peroxide.

Claims 14-26 (Canceled).